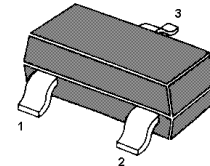
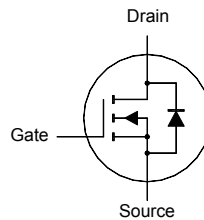


MMBT7002A

N-Channel Enhancement Mode Field Effect Transistor



1.Gate 2.Source 3.Drain
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Drain-Gate Voltage	V_{DG}	60	V
Gate-Source Voltage	V_{GS}	40	V
Drain Current	I_D	280	mA
Source-drain current	I_S	280	mA
Peak Drain Current	I_{DM}	1.5	A
Source-drain current (pulsed)	I_{SM}	1.5	A
Power Dissipation	P_D	350	mW
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
ISO 9001 : 2008 Certificate No. 02114012
OHSAS 18001 : 2007 Certificate No. 05121508008
IECQ QC 080000 Certificate No. E2418000714M02

Dated: 30/05/2016 Rev:01

MMBT7002A

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

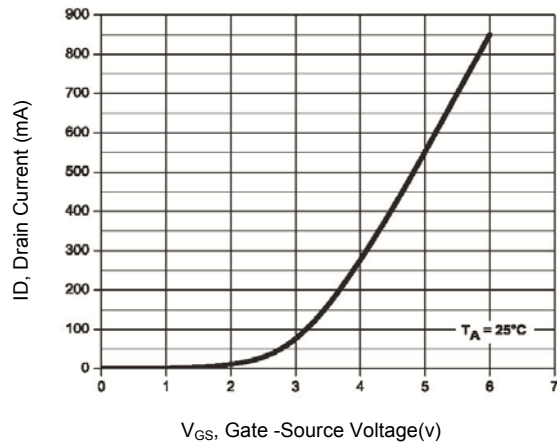
Parameter	Symbol	Min.	Max.	Unit
Drain Source Breakdown Voltage at $I_D = 10\text{ }\mu\text{A}$	BV_{DSS}	60	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 60\text{ V}$	I_{DSS}	-	1	μA
Zero Gate Voltage Drain Current at $V_{DS} = 60\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	I_{DSS}	-	500	μA
Gate Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	-	2.5	V
On-State Drain Current at $V_{GS} = 10\text{ V}$, $V_{DS} = 10\text{ V}$	$I_{D(ON)}$	500	-	mA
Drain-Source Diode Forward Voltage at $V_{GS} = 0$, $I_S = 400\text{ mA}$	V_{SD}	-	1.2	V
Drain-Source On-Voltage at $V_{GS} = 10\text{ V}$, $I_D = 500\text{ mA}$ at $V_{GS} = 5\text{ V}$, $I_D = 50\text{ mA}$	$V_{DS(ON)}$	- -	1 0.15	V V
Static Drain-Source On-Resistance at $V_{GS} = 10\text{ V}$, $I_D = 500\text{ mA}$	$R_{DS(ON)}$	-	2	Ω
Static Drain-Source On-Resistance at $V_{GS} = 10\text{ V}$, $I_D = 500\text{ mA}$, $T_J = 125\text{ }^{\circ}\text{C}$	$R_{DS(ON)}$	-	3.5	Ω
Static Drain-Source On-Resistance at $V_{GS} = 5\text{ V}$, $I_D = 50\text{ mA}$	$R_{DS(ON)}$	-	3	Ω
Static Drain-Source On-Resistance at $V_{GS} = 5\text{ V}$, $I_D = 50\text{ mA}$, $T_J = 125\text{ }^{\circ}\text{C}$	$R_{DS(ON)}$	-	5	Ω
Forward Transconductance at $V_{DS} = 10\text{ V}$, $I_D = 200\text{ mA}$	g_{FS}	80	-	mS
Input Capacitance at $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	50	pF
Output Capacitance at $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	25	pF
Reverse Transfer Capacitance at $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	5	pF
Turn-On Time at $V_{DD} = 30\text{ V}$, $R_G = 25\text{ }\Omega$, $I_D = 200\text{ mA}$, $V_{GS} = 10\text{ V}$, $R_L = 150\text{ }\Omega$	t_{on}	-	20	ns
Turn-Off Time at $V_{DD} = 30\text{ V}$, $R_G = 25\text{ }\Omega$, $I_D = 200\text{ mA}$, $V_{GS} = 10\text{ V}$, $R_L = 150\text{ }\Omega$	t_{off}	-	20	ns

TOP DYNAMIC

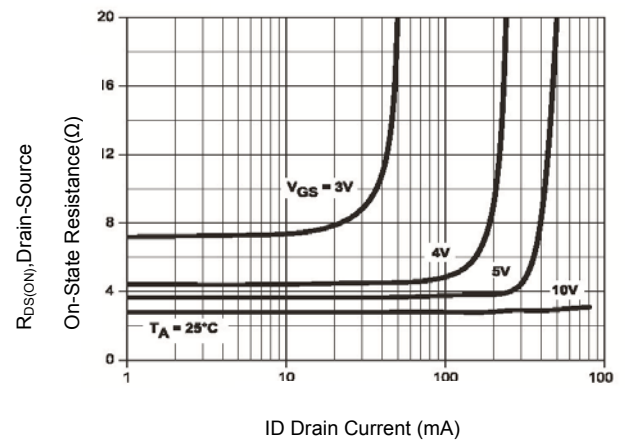


Dated: 30/05/2016 Rev:01

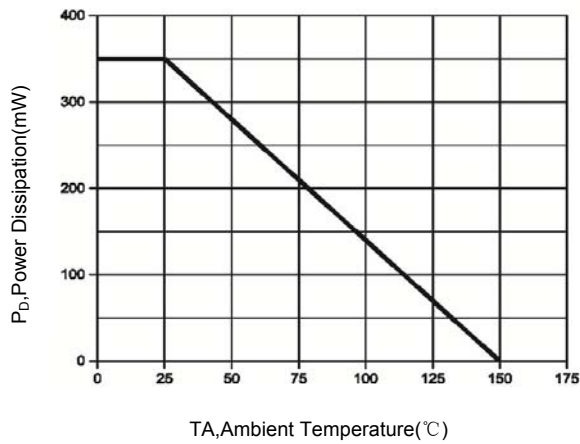
Transfer Characteristics



Drain Source On Resistance



Power Derating



Output Characteristics

